

#### 100V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET POWERDI1012-8

## **Product Summary**

BVDSS	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Tc = +25°C
100V	2.5mΩ @ V <sub>GS</sub> = 10V	215A

### **Features**

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production -Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low R<sub>DS(ON)</sub> Minimizes On State Losses
- Wettable Flank for Improved Optical Inspection
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/
- An Automotive-Compliant Part is Available Under Separate Datasheet (DMTH10H2M5STLWQ)

## **Description and Applications**

This new generation N-channel enhancement mode MOSFET is designed to minimize RDS(ON) yet maintain superior switching performance. This device is ideal for use in power management and load switch.

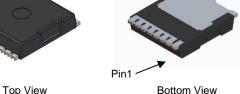
- Motor Control
- **DC-DC Converters**
- **Power Management**

#### **Mechanical Data**

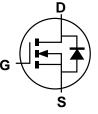
- Case: POWERDI®1012-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.388 grams (Approximate)

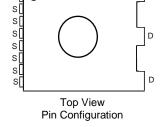






Internal Schematic





**Ordering Information** (Note 4)

Part Number	Case	Packaging
DMTH10H2M5STLW-13	POWERDI1012-8	1500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

# **Marking Information**



);; = Manufacturer's Marking TH10H2M5STL = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 21 = 2021) WW = Week Code (01 to 53)



## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage	VDSS	100	V	
Gate-Source Voltage	$V_{GSS}$	±20	V	
Continuous Drain Current (Note 6) $V_{GS} = 10V$ $T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$		ΙD	215 152	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	IDM	860	Α	
Maximum Continuous Body Diode Forward Current (Note 6)	Is	215	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	lsм	860	Α	
Avalanche Current, L = 0.3mH	las	68	Α	
Avalanche Energy, L = 0.3mH	Eas	701	mJ	

## **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5) $T_A = +25^{\circ}C$		P <sub>D</sub>	5.8	W
Thermal Resistance, Junction to Ambient (Note 5)		Reja	26	°C/W
Total Power Dissipation (Note 6) $T_C = +25^{\circ}C$		PD	230.8	W
Thermal Resistance, Junction to Case (Note 6)		Rejc	0.65	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +175	°C	

## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Tun	Max	Unit	Test Condition	
	Syllibol	IVIIII	Тур	IVIAX	Ullit	rest Condition	
OFF CHARACTERISTICS (Note 7)			,				
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100		_	V	$V_{GS} = 0V$ , $I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μΑ	$V_{DS} = 80V$ , $V_{GS} = 0V$	
Gate-Source Leakage	Igss	ı	_	±100	nA	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	Vgs(TH)	2	_	4	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	
Static Drain-Source On-Resistance	RDS(ON)	_	1.68	2.5	mΩ	Vgs = 10V, ID = 30A	
Diode Forward Voltage	VsD		0.8	1.2	V	V <sub>G</sub> S = 0V, I <sub>S</sub> = 30A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss		8450	_		V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V f = 1MHz	
Output Capacitance	Coss	_	2430	_	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>		17.7	_			
Gate Resistance	Rg		1.0		Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	Qg	_	124.4	_		V 50V I 00A	
Gate-Source Charge	Q <sub>gs</sub>		34	_	nC	V <sub>DD</sub> = 50V, I <sub>D</sub> = 30A, V <sub>GS</sub> = 10V	
Gate-Drain Charge	Q <sub>gd</sub>	1	28.3	_	l	VGS = 10V	
Turn-On Delay Time	t <sub>D</sub> (ON)		32.7	_			
Turn-On Rise Time	t <sub>R</sub>		47	_	no	$V_{DD} = 50V, V_{GS} = 10V,$	
Turn-Off Delay Time	tD(OFF)		91.3		ns	$I_D = 30A$ , $R_G = 4.7\Omega$	
Turn-Off Fall Time	t <sub>F</sub>	1	53.9	_			
Reverse Recovery Time	t <sub>RR</sub>	_	87.6	_	ns	I- 054 di/dt 4004/	
Reverse Recovery Charge	$Q_{RR}$	_	251.8	_	$nC$ IF = 25A, di/dt = 100A/ $\mu$ s		

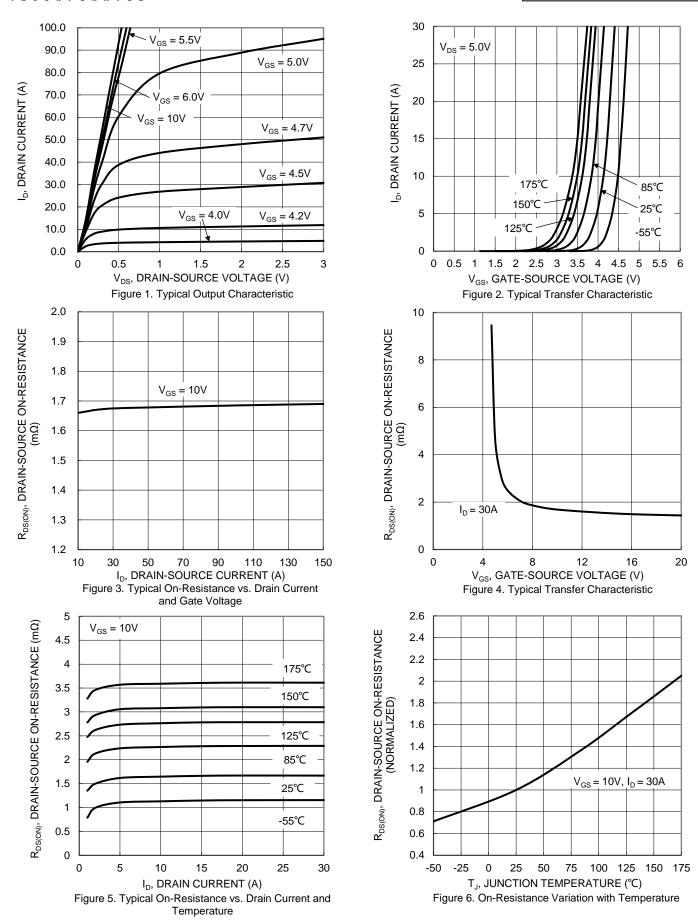
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate. 6. Thermal resistance from junction to soldering point (on the exposed drain pad).

7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.











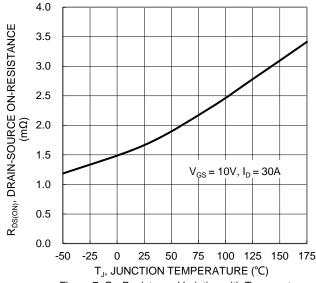
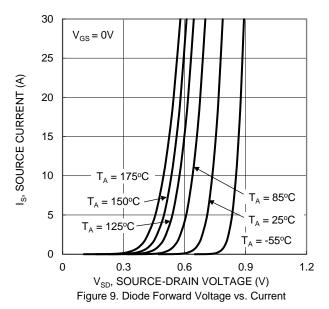


Figure 7. On-Resistance Variation with Temperature



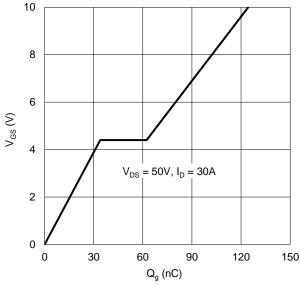


Figure 11. Gate Charge

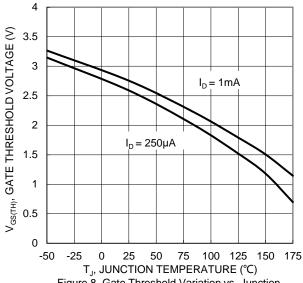
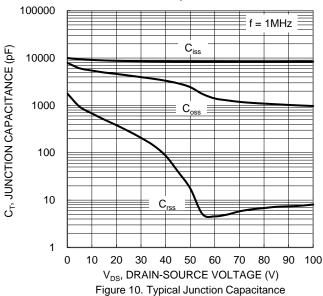


Figure 8. Gate Threshold Variation vs. Junction Temperature



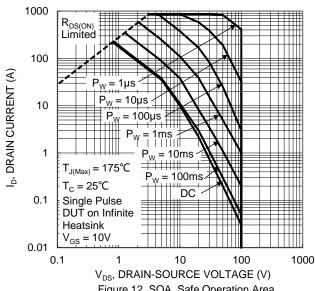


Figure 12. SOA, Safe Operation Area



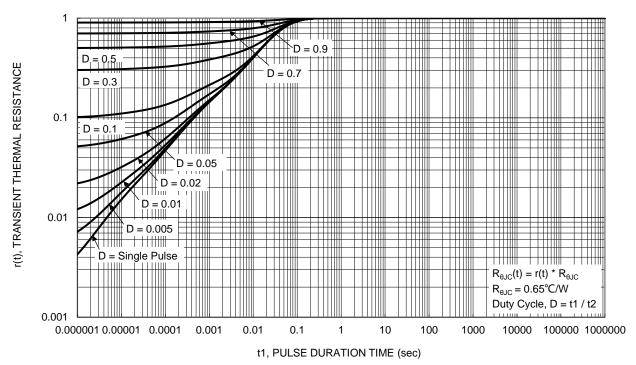


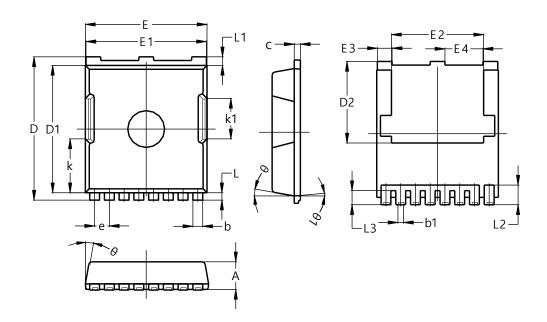
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### POWERDI1012-8

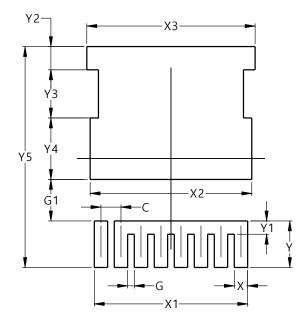


POWERDI1012-8					
Dim	Min	Max	Тур		
Α	2.20	2.40	2.30		
b	0.70	0.90	0.80		
b1	0.42	0.50	0.45		
C	0.40	0.60	0.50		
D	11.48	11.88	11.68		
D1	10.23	10.53	10.38		
D2	6.45	6.85	6.65		
Е	9.70	10.10	9.90		
E1	9.70	9.90	9.80		
E2	7.00	8.00	7.50		
E3	1.10	1.30	1.20		
E4	3.00	3.20	3.10		
е	1.20 BSC				
k	4.39 REF				
k1	3.30 REF				
٦	0.50	0.70	0.60		
L1	0.50	0.90	0.70		
L2	1.40	1.80	1.60		
L3	1.00	1.30	1.15		
θ	00	15º	10°		
θ1	00	10°	5º		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### POWERDI1012-8



Dimensions	Value (in mm)			
С	1.200			
G	0.400			
G1	2.500			
Х	0.800			
X1	9.200			
X2	9.700			
Х3	10.100			
Y	2.800			
Y1	0.800			
Y2	1.400			
Y3	2.900			
Y4	3.700			
Y5	13.300			



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